

Power Schottky rectifier

Features

- High junction temperature capability
- Optimized trade-off between leakage current and forward voltage drop
- Low leakage current
- Avalanche capability specified

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK and D²PAK, this device is particularly suited for use in notebook, game station, LCD TV and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 x 20 A
V_{RRM}	80 V
T_J (max)	175 °C
V_F (typ)	475 mV

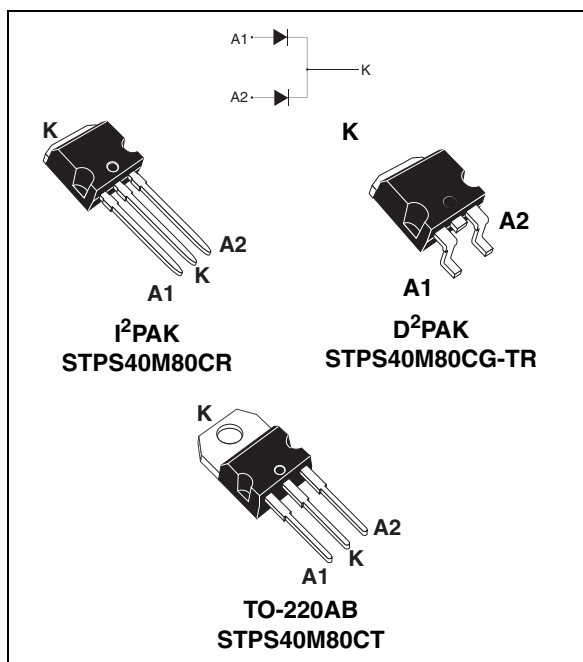
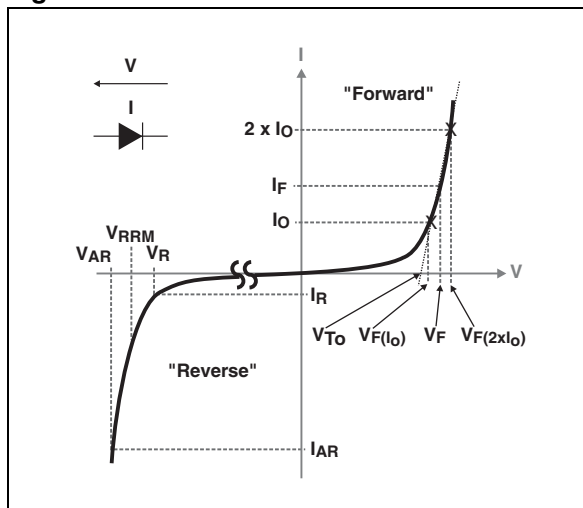


Figure 1. Electrical characteristics(a)



- a. V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in [Figure 11](#). V_{AR} and I_{AR} are pulse measurements ($t_p < 1 \mu s$). V_R , I_R , V_{RRM} and V_F , are static characteristics

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at $T_{amb} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			80	V
$I_{F(RMS)}$	Forward rms current			30	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 150\text{ °C}$ $T_c = 150\text{ °C}$	Per diode Per device	20 40	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms sinusoidal}$	$T_c = 25\text{ °C}$	200	A
$P_{ARM}^{(1)}$	Repetitive peak avalanche power	$T_j = 25\text{ °C}, t_p = 1\text{ }\mu\text{s}$		10000	W
$V_{ARM}^{(2)}$	Maximum repetitive peak avalanche voltage	$t_p < 1\text{ }\mu\text{s}, T_j < 150\text{ °C}, I_{AR} < 30\text{ A}$		100	V
$V_{ASM}^{(2)}$	Maximum single pulse peak avalanche voltage	$t_p < 1\text{ }\mu\text{s}, T_j < 150\text{ °C}, I_{AR} < 30\text{ A}$		100	V
T_{stg}	Storage temperature range			-65 to +175	°C
T_j	Maximum operating junction temperature ⁽³⁾			175	°C

1. For temperature or pulse time duration deratings, please refer to figure 3 and 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.
2. See [Figure 11](#)
3. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	per diode	1.30	°C/W
		total	0.75	
$R_{th(c)}$	Coupling		0.20	°C/W

When the two diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ }^\circ\text{C}$	$V_R = V_{RRM}$	-	15	65	μA
		$T_j = 125\text{ }^\circ\text{C}$		-	15	40	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ }^\circ\text{C}$	$I_F = 10\text{ A}$	-	0.550	0.600	V
		$T_j = 125\text{ }^\circ\text{C}$		-	0.475	0.510	
		$T_j = 25\text{ }^\circ\text{C}$	$I_F = 20\text{ A}$	-	0.655	0.735	
		$T_j = 125\text{ }^\circ\text{C}$		-	0.570	0.635	
		$T_j = 25\text{ }^\circ\text{C}$	$I_F = 40\text{ A}$	-	0.800	0.920	
		$T_j = 125\text{ }^\circ\text{C}$		-	0.680	0.795	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.475 \times I_{F(AV)} + 0.008 \times I_F^2(RMS)$$

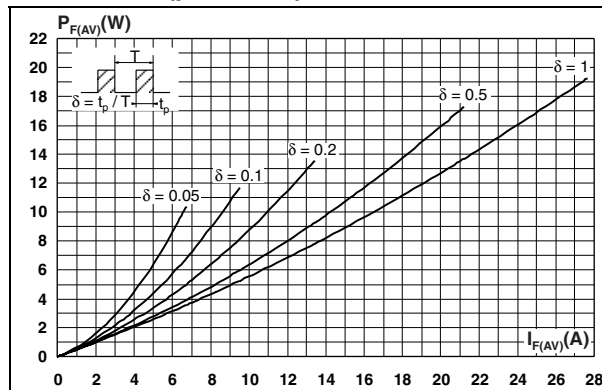
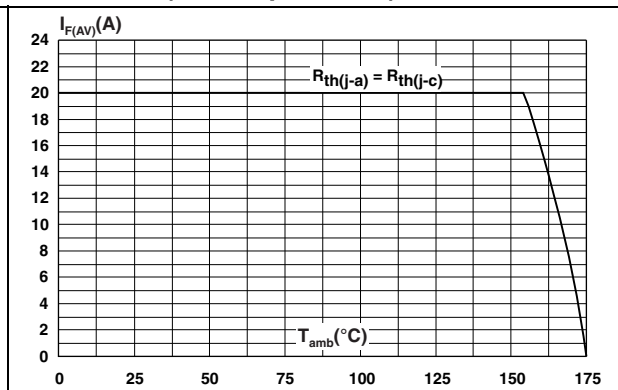
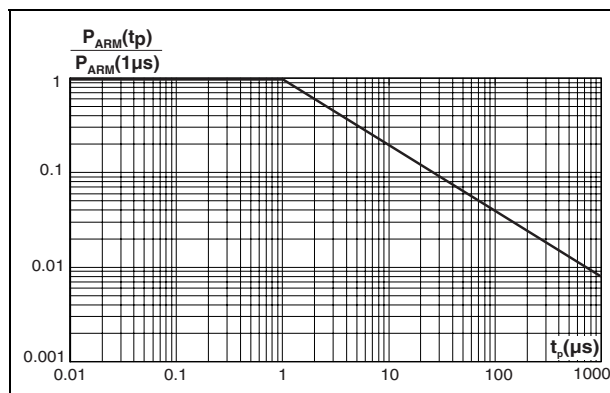
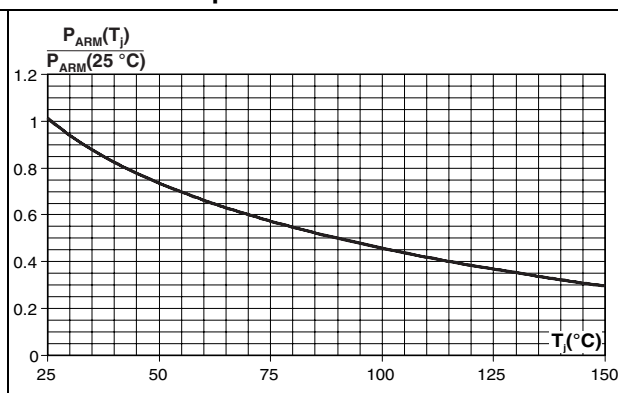
Figure 2. Average forward power dissipation versus average forward current (per diode)**Figure 3. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)****Figure 4. Normalized avalanche power derating versus pulse duration****Figure 5. Normalized avalanche power derating versus junction temperature**

Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

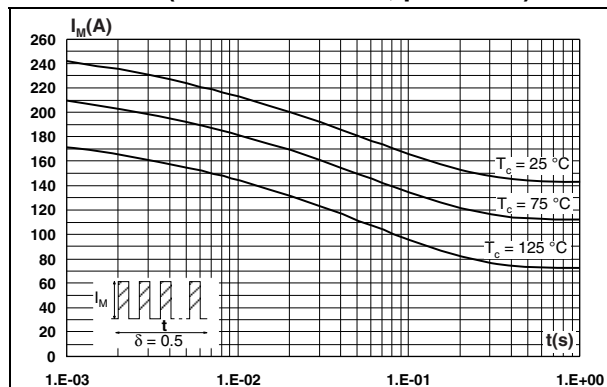


Figure 7. Relative thermal impedance junction to case versus pulse duration

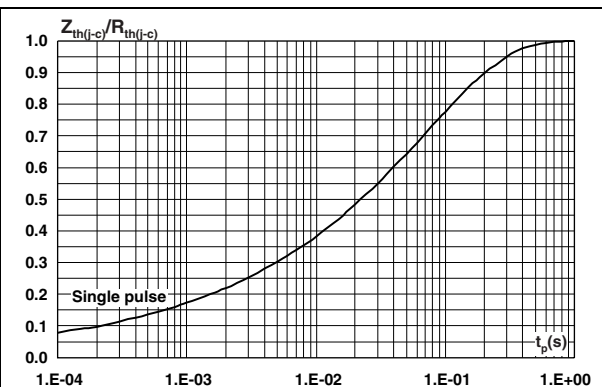


Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

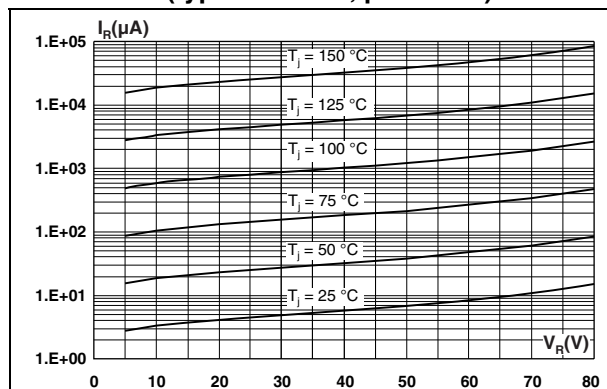


Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)

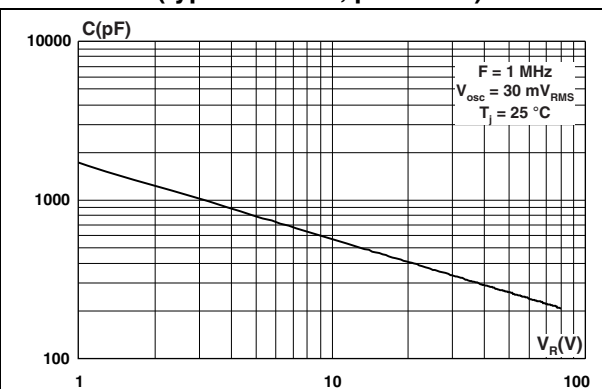


Figure 10. Forward voltage drop versus forward current (per diode)

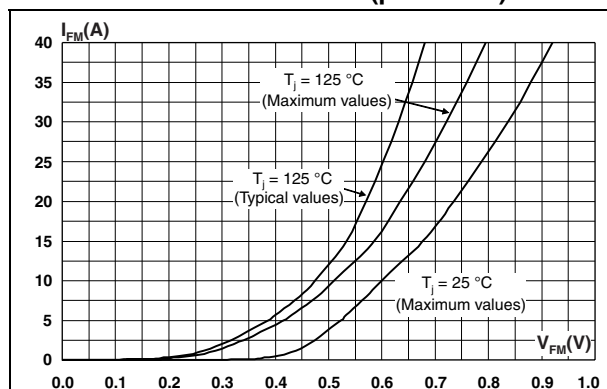


Figure 11. Reverse safe operating area (t_p < 1 μs and T_j < 150 °C)

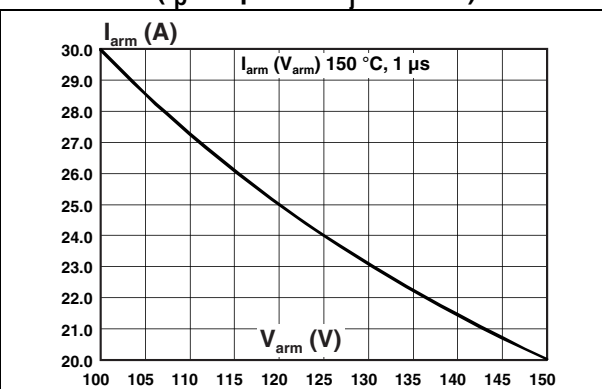
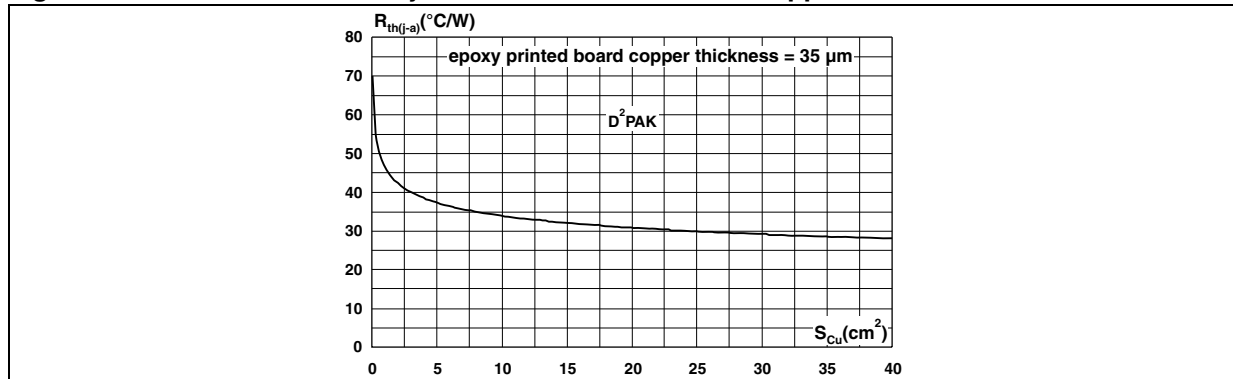


Figure 12. Thermal resistance junction to ambient versus copper surface under tab for D²PAK

2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 5. TO-220AB dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 Typ.		0.645 Typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 Typ.		0.102 Typ.	
Dia.	3.75	3.85	0.147	0.151

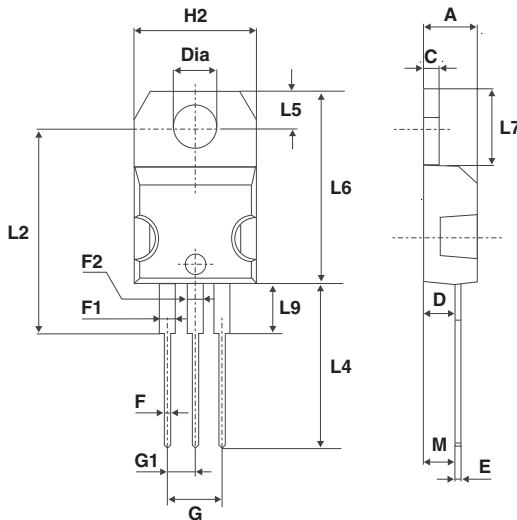


Table 6. D²PAK dimensions

Technical drawing of a Tee fitting, showing dimensions and a table of values.

Dimensions:

- A: Overall length of the Tee.
- A1: Length of the Tee from the centerline to the end of the branch.
- A2: Length of the Tee from the centerline to the end of the main run.
- B: Thickness of the Tee.
- B2: Thickness of the Tee at the branch.
- C: Radius of the Tee.
- C2: Radius of the Tee at the branch.
- D: Height of the Tee.
- E: Width of the Tee.
- G: Width of the Tee at the branch.
- L: Overall height of the Tee.
- L2: Height of the Tee from the centerline to the top of the main run.
- L3: Height of the Tee from the centerline to the top of the branch.
- M: Thickness of the Tee at the branch.
- R: Radius of the Tee.
- V2: Angle of the Tee.

Table of Values:

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

* FLAT ZONE NO LESS THAN 2mm

Figure 13. D²PAK footprint (dimensions in mm)

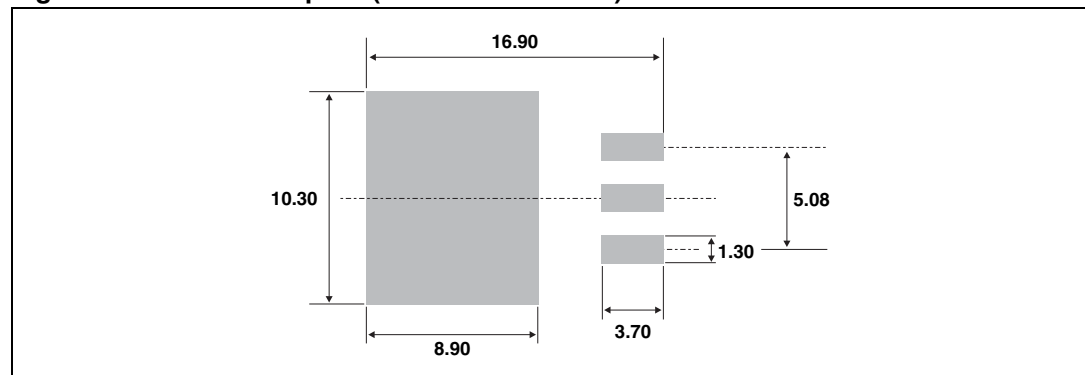
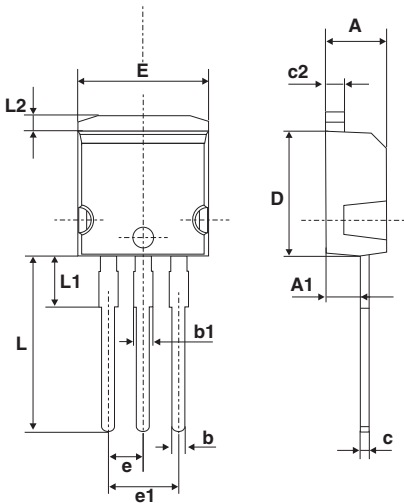


Table 7. I²PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055



3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40M80CT	STPS40M80CT	TO-220AB	1.9 g	50	Tube
STPS40M80CR	STPS40M80CR	I ² PAK	1.49 g	50	Tube
STPS40M80CG-TR	STPS40M80CG	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

Table 9. Revision history

Date	Revision	Changes
11-Apr-2011	1	First issue.

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